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09 February 2017

Micron recently revealed to investors it will start producing GDDR6 memory on H2 2017, pushing forward to previously announced 2018 launch window.



GDDR6 represents a leap in memory technology, as Micron says it is capable of speeds reaching 16GB/s per pin, around 10x faster than mainstream memory. In comparison, the most refined version of GDDR5 offers throughput reaching 8GB/s per pin (up from an initial 4GB/s), while last year's GDDR5X increased speeds to 10GB/s per pin.

In addition the company says GDDR6 consumes 20% less power, making it ideal for mobile PCs with limited untethered battery life. The company expects to release the memory technology by end 2017, and estimates it will almost completely replace GDDR5 in PC and game console graphics by 2020.

Other Micron news announced to investors includes the company's transition to 20nm DRAM, as well as further work on 1Xnm DRAM. Such drops in the lithography process bring about reduced fabrication costs-- the jump from 25nm to 20nm brought savings of 25%, and the savings are set to increase by an additional 20% with 1Xnm.

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